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BLP05H635XR; BLP05H635XRG

Power LDMOS transistor

AMPLEON

Rev. 4 — 21 September 2016

Product data sheet

1. Product profile

1.1 General description

A 35 W extremely rugged LDMOS power transistor for broadcast and industrial applications in the HF to 600 MHz band.

Table 1. Application information

Test signal	f	V _{DS}	PL	Gp	η _D
	(MHz)	(V)	(W)	(dB)	(%)
pulsed RF	108	50	35	27	75
CW	63.86	50	35	29.4	75.6
	127.72	50	35	26.8	75.7

1.2 Features and benefits

- Easy power control
- Integrated double sided ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (HF to 600 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outlin	e Graphic symbol
BLP05H6	35XR (SOT1223-2)		
1	gate 2		
2	gate 1	4 3	. 🗀
3	drain 1		
4	drain 2	pin 1 index	5
5	source	[1]	2
		1 2	3
			aaa-003574
BLP05H6	35XRG (SOT1224-2)		
1	gate 2		
2	gate 1	4 3	_
3	drain 1	□ ○ pin 1 index ○	
4	drain 2	pin 1 index	5
5	source	[1] 1 2	
			' 3
			aaa-003574

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
BLP05H635XR	HSOP4F	plastic, heatsink small outline package; 4 leads (flat)	SOT1223-2	
BLP05H635XRG	HSOP4F	plastic, heatsink small outline package; 4 leads	SOT1224-2	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	135	V
V_{GS}	gate-source voltage		-6	+11	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

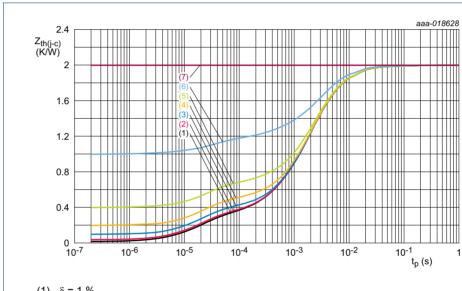
BLP05H635XR_H635XRG

Thermal characteristics 5.

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions		Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T _j = 115 °C	[1][2]	2.0	K/W
Z _{th(j-c)}	transient thermal impedance from junction to case	T_j = 150 °C; t_p = 100 μs; δ = 20 %	[3]	0.68	K/W

- [1] T_i is the junction temperature.
- R_{th(j-c)} is measured under RF conditions.
- See Figure 1.



- (1) $\delta = 1 \%$
- (2) $\delta = 2 \%$
- (3) $\delta = 5 \%$
- (4) $\delta = 10 \%$
- (5) $\delta = 20 \%$
- (6) $\delta = 50 \%$
- (7) $\delta = 100 \% (DC)$

Fig 1. Transient thermal impedance from junction to case as a function of pulse duration

Characteristics 6.

DC characteristics Table 6.

 T_i = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.125 \text{ mA}$	135	-	-	V
V _{GS(th)}	gate-source threshold voltage	V_{DS} = 10 V; I_{D} = 12.5 mA	1.25	1.8	2.25	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 50 \text{ V}; I_{D} = 10 \text{ mA}$	-	1.7	-	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 50 V	-	-	1.4	μΑ

BLP05H635XR_H635XRG

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Table 6. DC characteristics ...continued

 T_i = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	1.8	-	Α
I _{GSS}	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	140	nA
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 437.5 \text{ mA}$	-	3.2	-	Ω

Table 7. AC characteristics

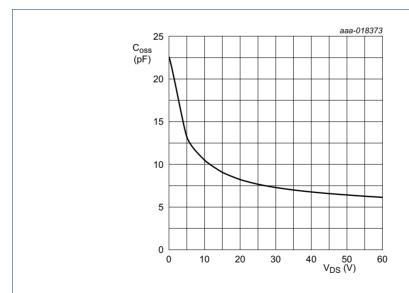
 T_i = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{rs}	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	0.12	-	pF
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	16.2	-	pF
Coss	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	6.4	-	pF

Table 8. RF characteristics

Test signal: pulsed RF; t_p = 100 μ s; δ = 20 %; f = 108 MHz; RF performance at V_{DS} = 50 V; I_{Dq} = 10 mA; T_{case} = 25 $^{\circ}$ C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G_p	power gain	P _L = 35 W	25.5	27	-	dB
RLin	input return loss	P _L = 35 W	-	-25	-	dB
η_{D}	drain efficiency	P _L = 35 W	71	75	-	%



 $V_{GS} = 0 V$; f = 1 MHz.

Fig 2. Output capacitance as a function of drain-source voltage; typical values per section

7. Test information

7.1 Ruggedness in class-AB operation

The BLP05H635XR and BLP05H635XRG are capable of withstanding a load mismatch corresponding to VSWR > 65 : 1 through all phases under the following conditions: $V_{DS} = 50 \text{ V}$; $I_{Dq} = 20 \text{ mA}$; $P_L = 35 \text{ W pulsed}$; f = 108 MHz.

7.2 Impedance information

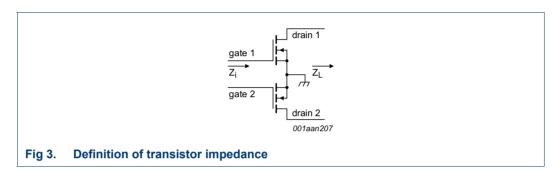


Table 9. Typical push-pull impedance

Simulated Z_i and Z_L device impedance; impedance info at $V_{DS} = 50 \text{ V}$ and $P_L = 35 \text{ W}$.

f	Z _i	Z_L
(MHz)	(Ω)	(Ω)
108	46.6 – j282.0	100.6 + j26.9

7.3 UIS avalanche energy

Table 10. Typical avalanche data per section

 T_{amb} = 25 °C; typical test data; test jig without water cooling.

las	E _{AS}
(A)	(J)
1.0	0.08
1.25	0.05
1.5	0.04

For information see application note AN10273.

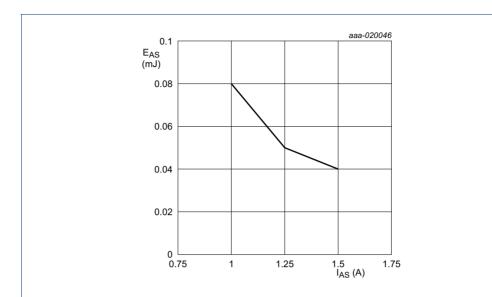
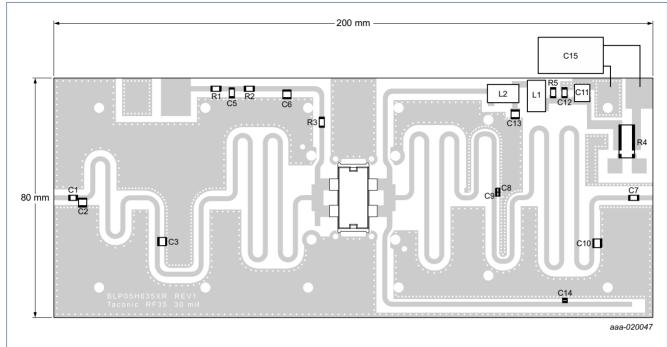


Fig 4. Non-repetitive avalanche energy as a function of single pulse avalanche current; typical values

7.4 Test circuit



Printed-Circuit Board (PCB): RF-35; ϵ_r = 3.5 F/m; thickness = 0.765 mm; thickness copper plating = 35 μ m. See <u>Table 11</u> for a list of components.

Fig 5. Component layout for class-AB production test circuit

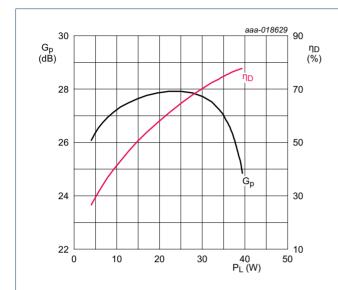
Table 11. List of components For test circuit see Figure 5.

Component	Description	Value	Remarks
C1, C7	multilayer ceramic chip capacitor	470 pF	ATC 800B
C2	multilayer ceramic chip capacitor	120 pF	ATC 800B
C3	multilayer ceramic chip capacitor	390 pF	ATC 800B
C5	multilayer ceramic chip capacitor	1 μF, 50 V	GRM32RR71H105KA01L
C6, C13	multilayer ceramic chip capacitor	820 pF	ATC 800B
C8, C9	multilayer ceramic chip capacitor	39 pF	ATC 100A
C10	multilayer ceramic chip capacitor	27 pF	ATC 800B
C11	multilayer ceramic chip capacitor	4.7 μF, 100 V	C5750X7RA475KT/A
C12	multilayer ceramic chip capacitor	100 nF	GRM188R72A104KA35D
C14	multilayer ceramic chip capacitor	15 pF	ATC 800B
C15	electrolytic capacitor	2200 μF, 63 V	Vishay
L1	wire inductor	169 nH	Coilcraft:132-12SMG
L2	wire inductor	90 nH	Coilcraft:132-9SMG
R1, R2	resistor	10 Ω	SMD 1206
R3	resistor	4.64 kΩ	SMD 0805
R4	shunt resistor	50 mΩ	Ohmite: FC4L110R050FER
R5	resistor	7.5 Ω, 0.6 W	SMD 1206

7.5 Graphical data

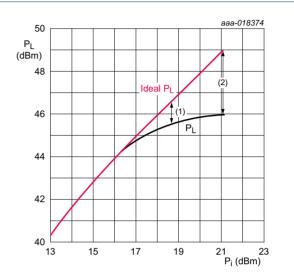
The following figures are measured in a class-AB production test circuit.

7.5.1 1-Tone CW pulsed



 V_{DS} = 50 V; I_{Dq} = 10 mA; f = 108 MHz; t_p = 100 $\mu s;$ δ = 20 %.

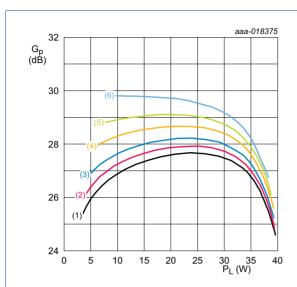
Fig 6. Power gain and drain efficiency as function of output power; typical values



 V_{DS} = 50 V; I_{Dq} = 10 mA; f = 108 MHz; t_p = 100 $\mu s;$ δ = 20 %.

- (1) $P_{L(1dB)} = 45.5 \text{ dBm}$ (35.2 W) at $P_i = 18.6 \text{ dBm}$
- (2) $P_{L(3dB)} = 46.0 \text{ dBm}$ (39.4 W) at $P_i = 21.1 \text{ dBm}$

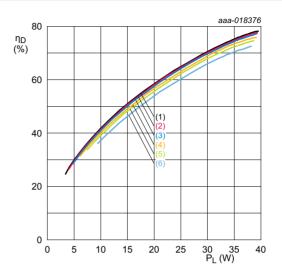
Fig 7. Output power as a function of input power; typical values



 V_{DS} = 50 V; f = 108 MHz; t_p = 100 $\mu s;$ δ = 20 %.

- (1) $I_{Dq} = 5 \text{ mA}$
- (2) $I_{Dq} = 10 \text{ mA}$
- (3) $I_{Dq} = 20 \text{ mA}$
- (4) $I_{Dq} = 50 \text{ mA}$
- (5) $I_{Dq} = 100 \text{ mA}$
- (6) $I_{Dq} = 200 \text{ mA}$

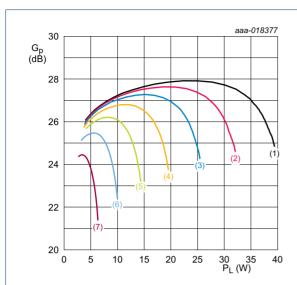
Fig 8. Power gain as a function of output power; typical values



 V_{DS} = 50 V; f = 108 MHz; t_p = 100 $\mu s;$ δ = 20 %.

- (1) $I_{Dq} = 5 \text{ mA}$
- (2) $I_{Dq} = 10 \text{ mA}$
- (3) $I_{Dq} = 20 \text{ mA}$
- (4) $I_{Dq} = 50 \text{ mA}$
- (5) $I_{Dq} = 100 \text{ mA}$
- (6) $I_{Dq} = 200 \text{ mA}$

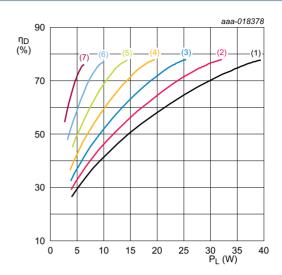
Fig 9. Drain efficiency as a function of output power; typical values



 I_{Dq} = 10 mA; f = 108 MHz; t_p = 100 $\mu s;$ δ = 20 %.

- (1) $V_{DS} = 50 \text{ V}$
- (2) $V_{DS} = 45 \text{ V}$
- (3) $V_{DS} = 40 \text{ V}$
- (4) $V_{DS} = 35 \text{ V}$
- (5) $V_{DS} = 30 \text{ V}$
- (6) $V_{DS} = 25 \text{ V}$
- (7) $V_{DS} = 20 \text{ V}$

Fig 10. Power gain as a function of output power; typical values



 I_{Dq} = 10 mA; f = 108 MHz; t_p = 100 $\mu s;$ δ = 20 %.

- (1) $V_{DS} = 50 \text{ V}$
- (2) $V_{DS} = 45 \text{ V}$
- (3) $V_{DS} = 40 \text{ V}$
- (4) $V_{DS} = 35 V$
- (5) $V_{DS} = 30 \text{ V}$
- (6) $V_{DS} = 25 V$
- (7) $V_{DS} = 20 \text{ V}$

Fig 11. Drain efficiency as a function of output power; typical values

8. Package outline

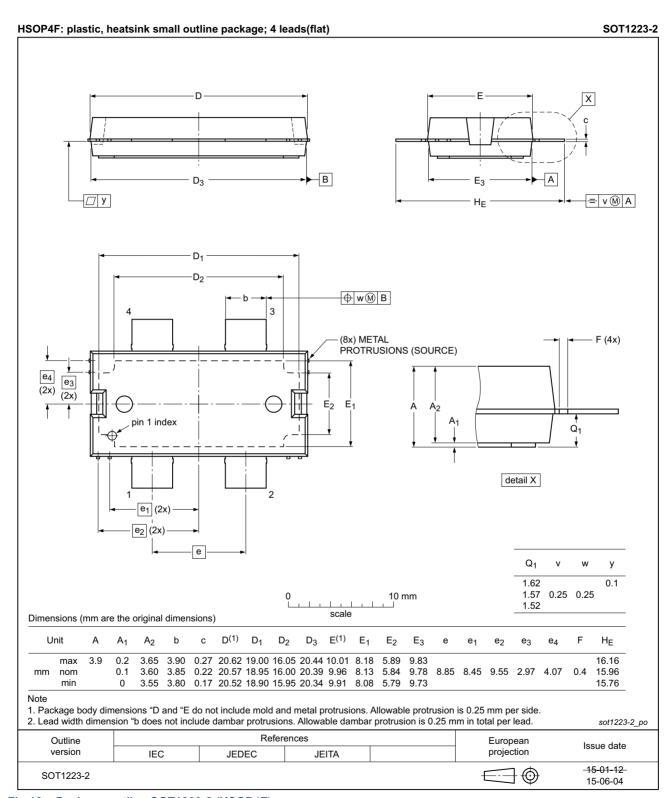


Fig 12. Package outline SOT1223-2 (HSOP4F)

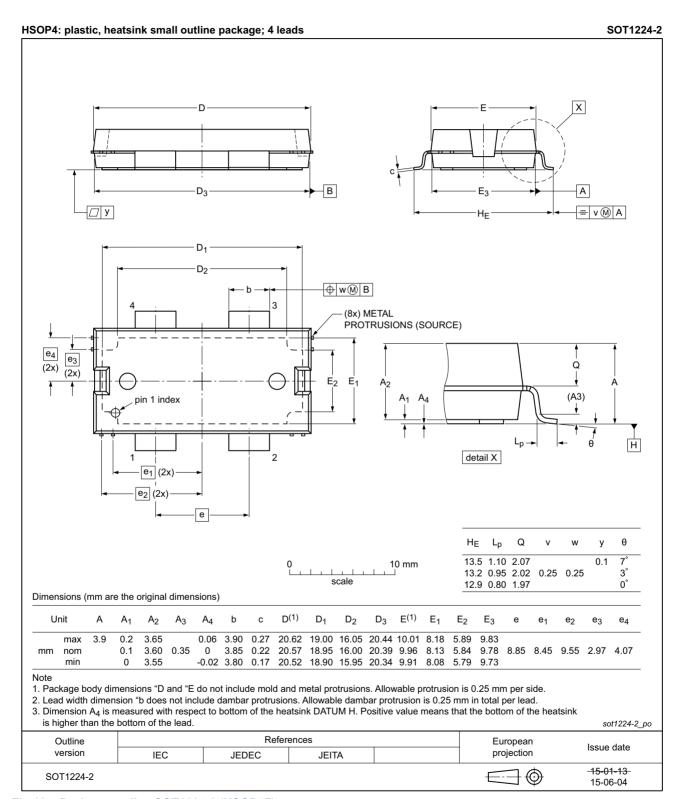


Fig 13. Package outline SOT1224-2 (HSOP4F)

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

10. Abbreviations

Table 12. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
SMD	Surface Mounted Device
UIS	Unclamped Inductive Switching
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLP05H635XR_H635XRG v.4	20160921	Product data sheet	-	BLP05H635XR v.3	
Modifications:	 The document now describes both the straight lead and gull-wing versions of this product: BLP05H635XR and BLP05H635XRG respectively 				
	• Table 2 on page 2: added BLP05H635XRG data				
	<u>Table 3 on page 2</u> : added BLP05H635XRG data				
	Section 7.1 on page 5: added BLP05H635XRG				
	• Figure 13 o	n page 12: added figure	SOT1224-2		
BLP05H635XR v.3	20160108	Product data sheet	-	BLP05H635XR#2	
BLP05H635XR#2	20150901	Objective data sheet	-	BLP05H635XR v.1	
BLP05H635XR v.1	20150518	Objective data sheet	-	-	

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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Power LDMOS transistor

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Power LDMOS transistor

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